



STB9NB50

N-CHANNEL 500V - 0.75 Ω - 8.6A D²PAK STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB9NB50	500 V	<0.85 Ω	8.6 A

- TYPICAL R_{DS(on)} = 0.75 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100 °C
- VERY LOW INTRINSIC CAPACITANCE
- GATE CHARGE MINIMIZED
- LOW LEAKAGE CURRENT
- APPLICATION ORIENTED
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

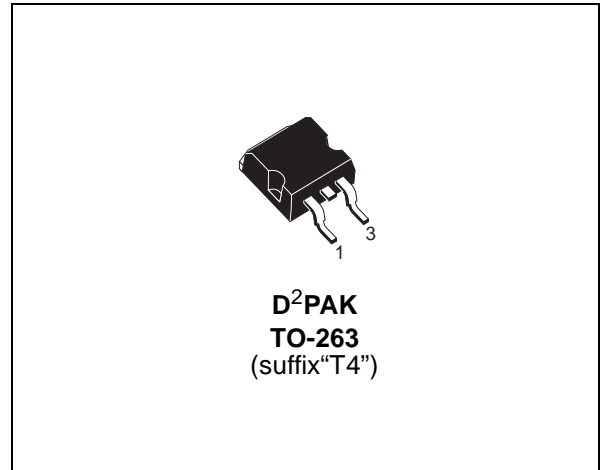
- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY (UPS)

ABSOLUTE MAXIMUM RATINGS

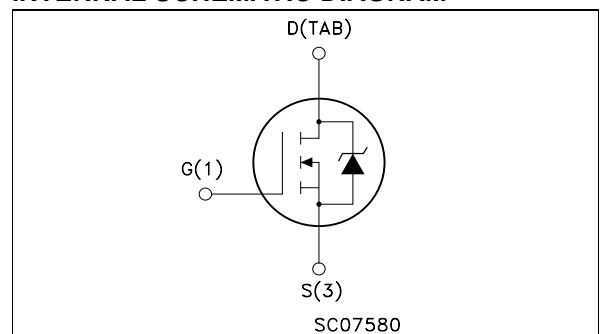
Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate- source Voltage	± 30	V
I _D	Drain Current (continuous) at T _C = 25°C	8.6	A
I _D	Drain Current (continuous) at T _C = 100°C	5.4	A
I _{DM} (●)	Drain Current (pulsed)	34.4	A
P _{tot}	Total Dissipation at T _C = 25°C	125	W
	Derating Factor	1.0	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	4.5	V/ns
T _{stg}	Storage Temperature	-60 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area.

(2) I_{SD} ≤ 9A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.



INTERNAL SCHEMATIC DIAGRAM



STB9NB50

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	°C/W
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.5	°C/W
T_j	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	8.6	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	520	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	500			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30\text{ V}$			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 4.3\text{ A}$		0.75	0.85	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	8.6			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(*)}$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 4.3\text{ A}$	4.5	5.7		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$		1250	1625	pF
C_{oss}	Output Capacitance			175	236	pF
C_{rss}	Reverse Transfer Capacitances			20	27	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 250V$ $I_D = 4.3 A$ $R_G = 4.7 \Omega$ $V_{GS} = 10 V$ (see test circuit, Figure 3)		19 11	30 15	ns ns
Q_g	Total Gate Charge	$V_{DD}=400V$ $I_D=8.6A$ $V_{GS}=10V$		32	45	nC
Q_{gs}	Gate-Source Charge			10.6		nC
Q_{gd}	Gate-Drain Charge			13.7		nC

SWITCHING OFF

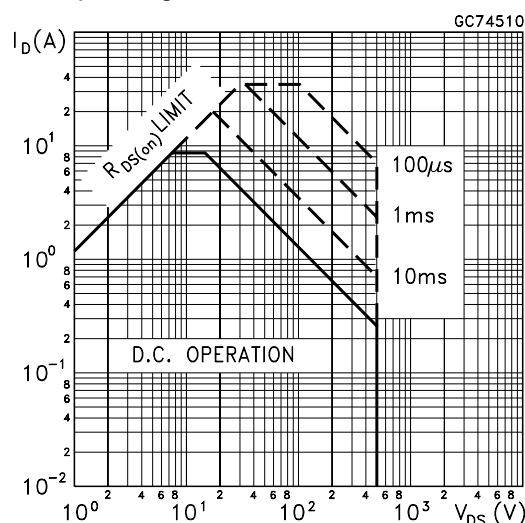
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 400 V$ $I_D = 8.6 A$ $R_G = 4.7 \Omega$ $V_{GS} = 10 V$ (see test circuit, Figure 5)		11.5 11 20	17 16 28	ns ns ns

SOURCE DRAIN DIODE

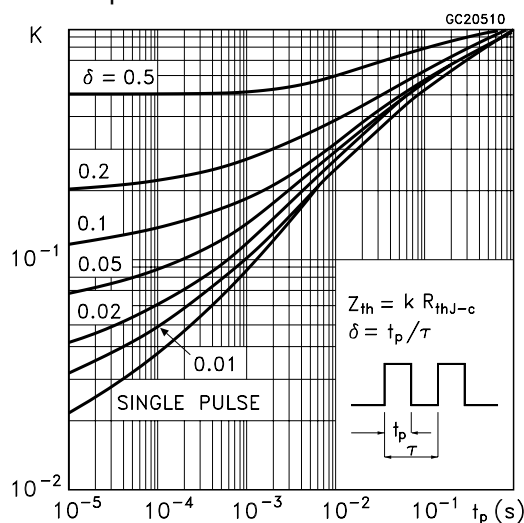
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8.6	A
$I_{SDM} (\bullet)$	Source-drain Current (pulsed)				34.4	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 8.6 A$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 8.6 A$ $di/dt = 100 A/\mu s$ $V_{DD} = 100V$ $T_j = 150 \text{ }^\circ C$ (see test circuit, Figure 3)		420 3.5 16.5		ns μC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 (•) Pulse width limited by safe operating area.

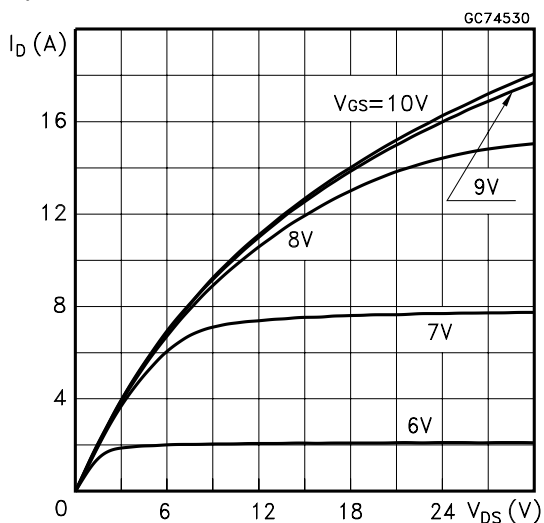
Safe Operating Area



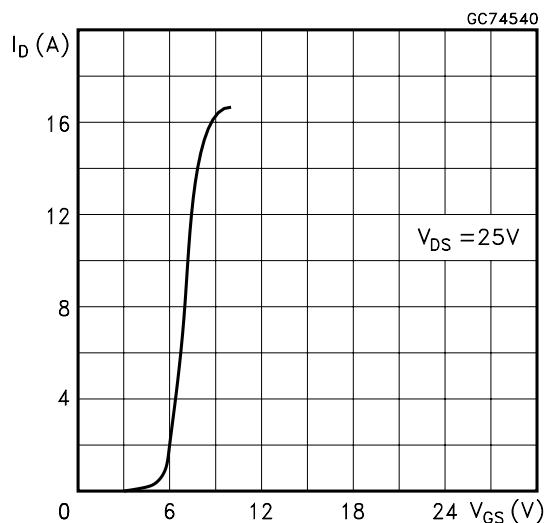
Thermal Impedance



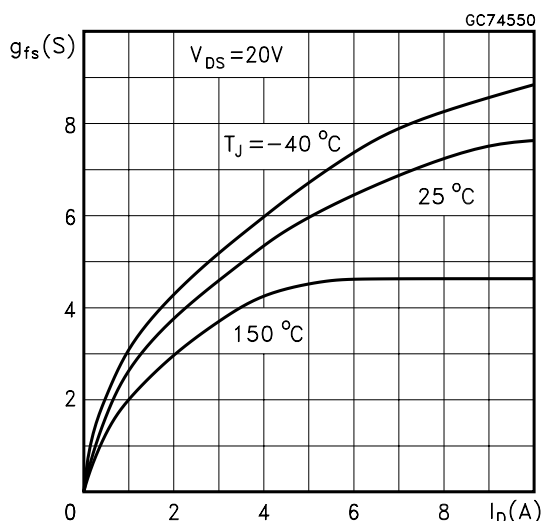
Output Characteristics



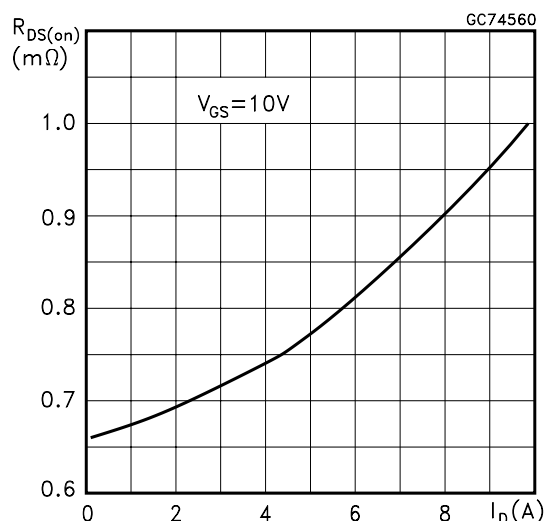
Transfer Characteristics



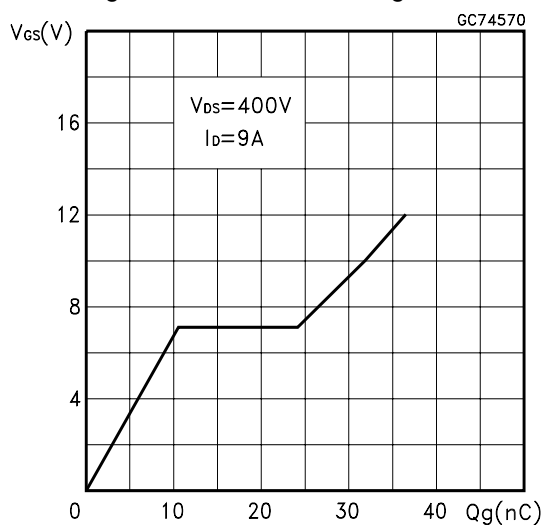
Transconductance



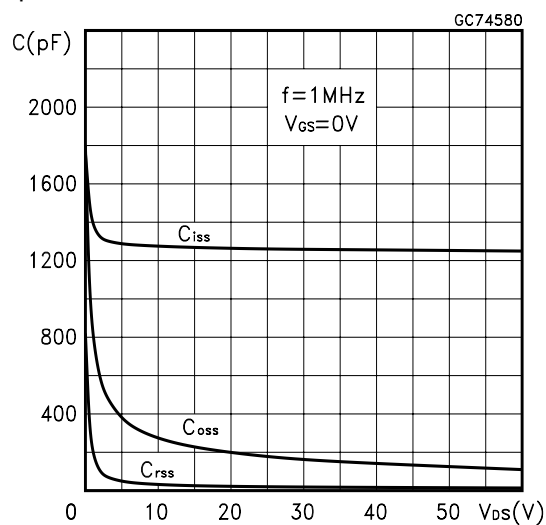
Static Drain-source On Resistance



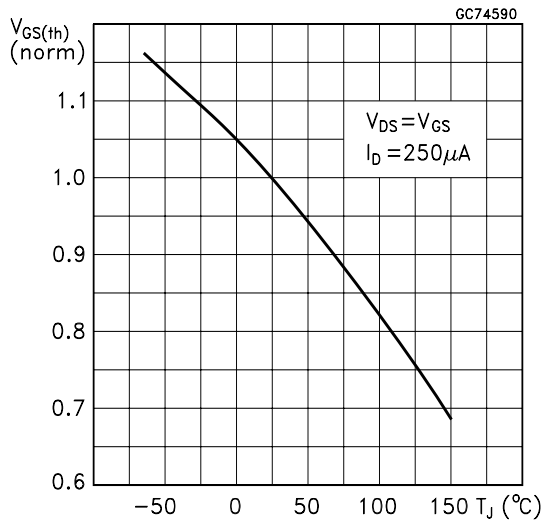
Gate Charge vs Gate-source Voltage



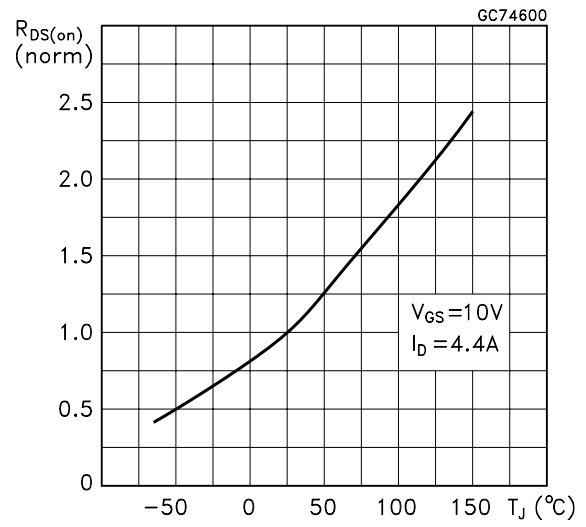
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

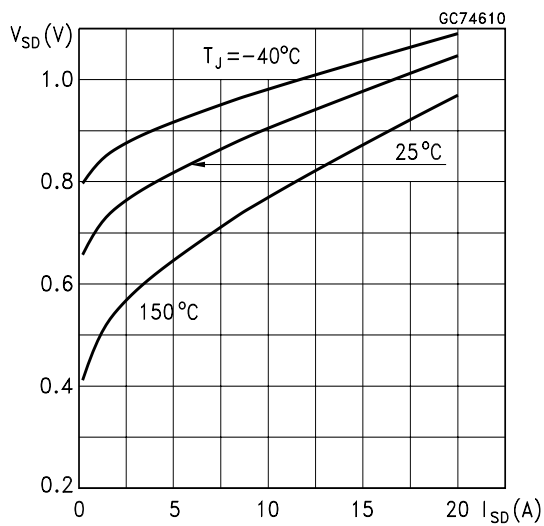


Fig. 1: Unclamped Inductive Load Test Circuit

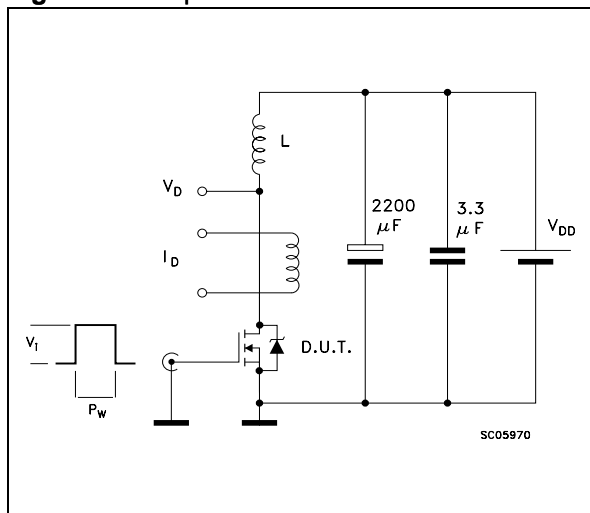


Fig. 2: Unclamped Inductive Waveform

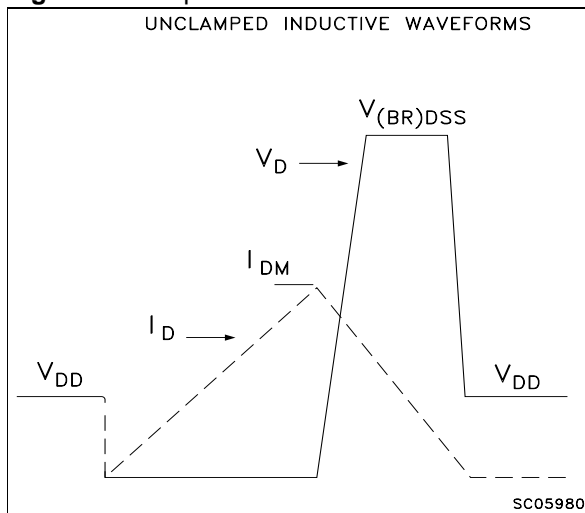


Fig. 3: Switching Times Test Circuits For Resistive Load

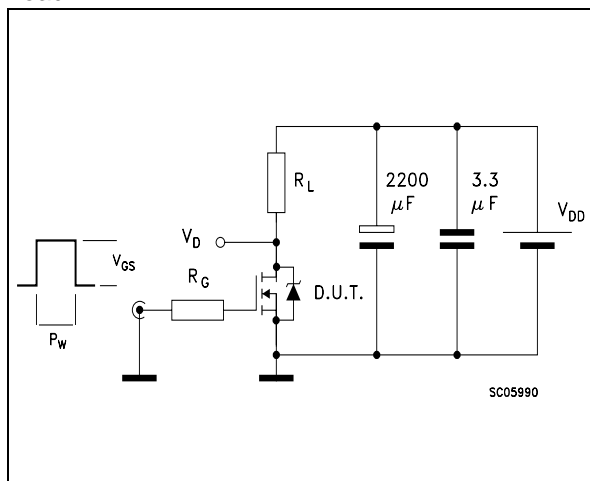


Fig. 4: Gate Charge test Circuit

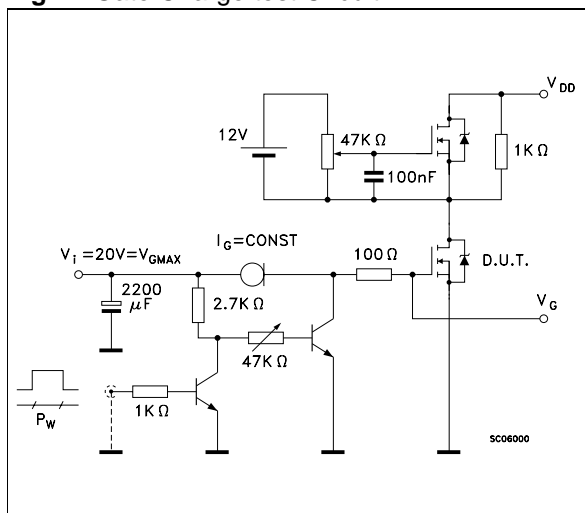
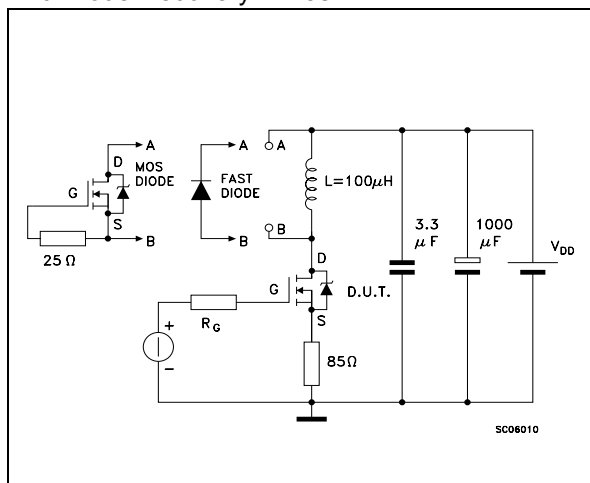
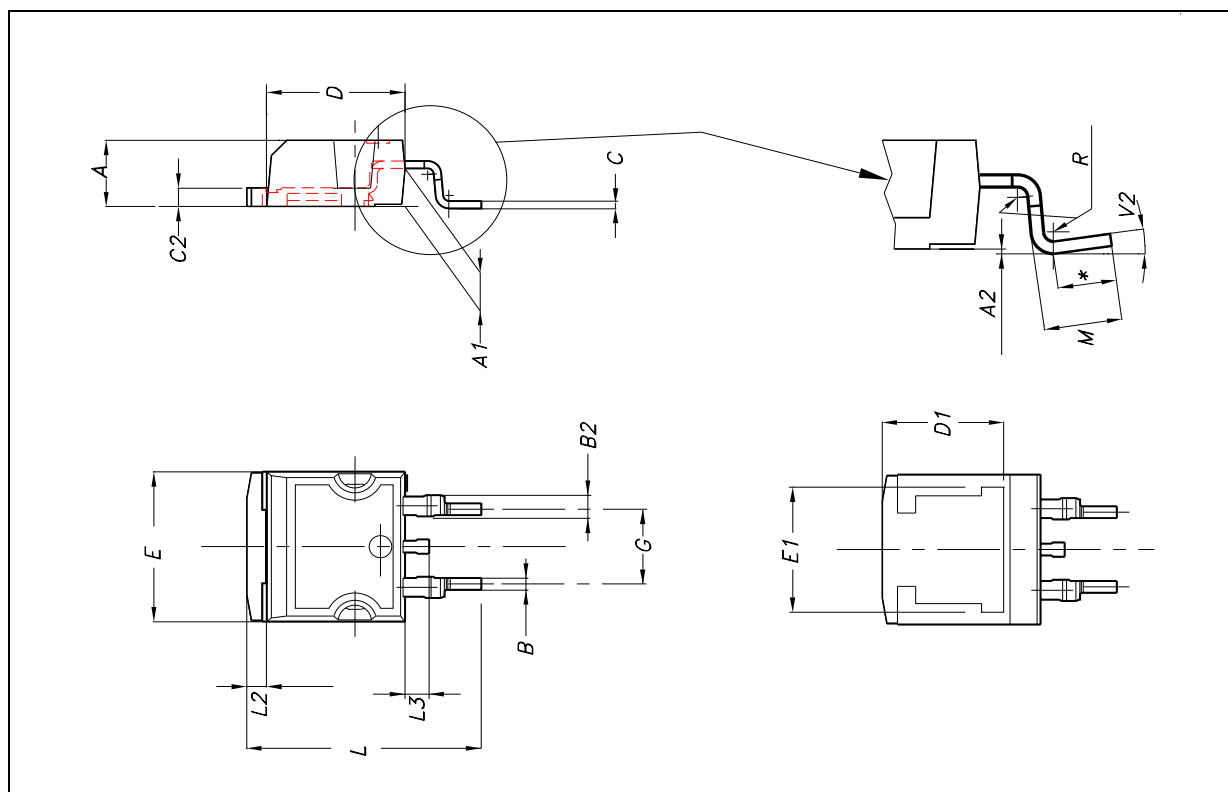


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



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